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Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-40	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	-24	A
I _D	Continuous Drain Current	T _C =25°C	-30*	A
		T _C =100°C	-30*	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	-120*	A
P _D	Maximum Power Dissipation	T _C =25°C	42	W
		T _C =100°C	17	
R _{θJC}	Thermal Resistance-Junction to Case		3	°C/W
I _D	Continuous Drain Current	T _A =25°C	-9.3	A
		T _A =70°C	-7.4	
P _D	Maximum Power Dissipation	T _A =25°C	1.6	W
		T _A =70°C	1	
R _{θJA} ^c	Thermal Resistance-Junction to Ambient		80	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	-24	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	144	mJ

Note * : Current limited by bonding wire.

Note a : Pulse width limited by maximum junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature (initial temperature $T_J=25^{\circ}\text{C}$).

Note c : Surface mounted on 1in^2 pad area.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

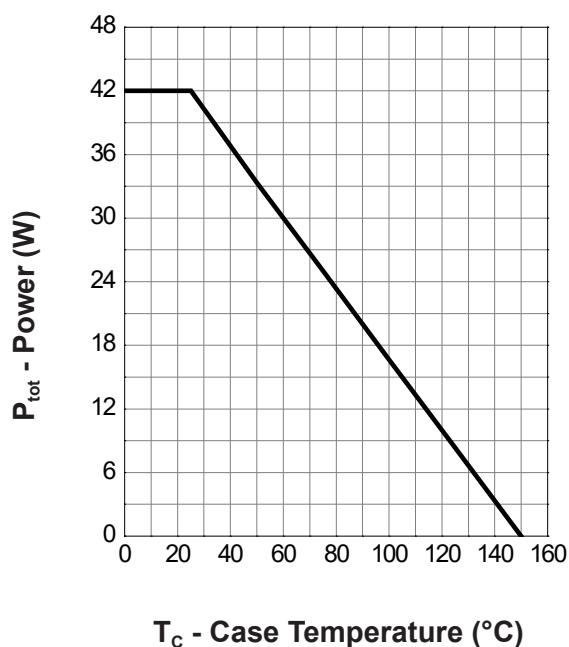
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-32V, V _{GS} =0V	-	-	-1	μA
		T _J =85°C	-	-	-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.5	-2	-2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±10	μA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-16A	-	9	10.8	mΩ
		V _{GS} =-4.5V, I _{DS} =-10A	-	13	16.7	
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.75	-1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-16A, dI _{SD} /dt=100A/μs	-	29	-	ns
Q _{rr}	Reverse Recovery Charge		-	24	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	2.9	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-20V, Frequency=1.0MHz	-	2840	3692	pF
C _{oss}	Output Capacitance		-	415	-	
C _{rss}	Reverse Transfer Capacitance		-	285	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-20V, R _L =20Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	18	33	ns
t _r	Turn-on Rise Time		-	16	29	
t _{d(OFF)}	Turn-off Delay Time		-	94	170	
t _f	Turn-off Fall Time		-	50	90	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =-20V, V _{GS} =-4.5V, I _{DS} =-16A	-	32	44	nC
Q _g	Total Gate Charge	V _{DS} =-20V, V _{GS} =-10V, I _{DS} =-16A	-	62	-	
Q _{gs}	Gate-Source Charge		-	9	-	
Q _{gd}	Gate-Drain Charge		-	17	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

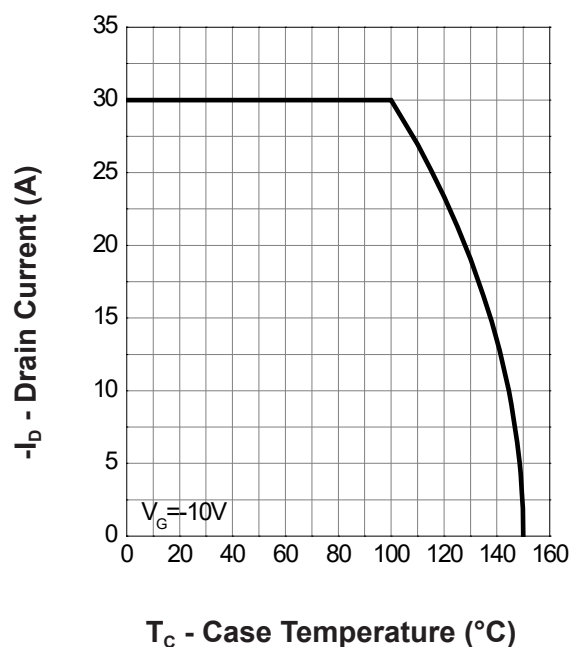
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

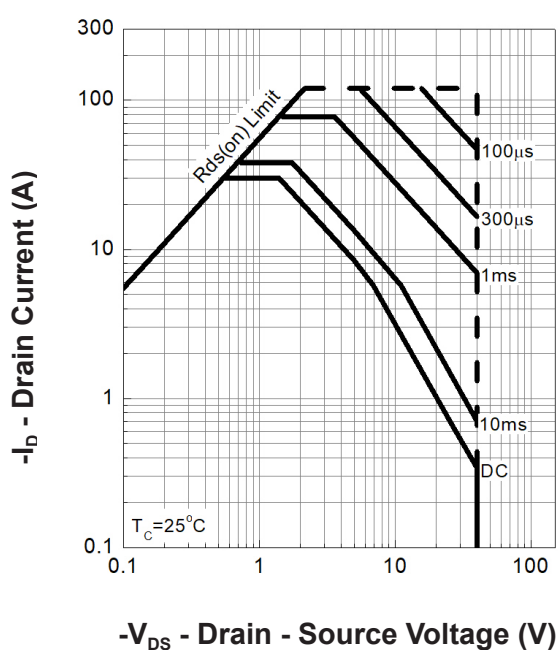
Power Dissipation



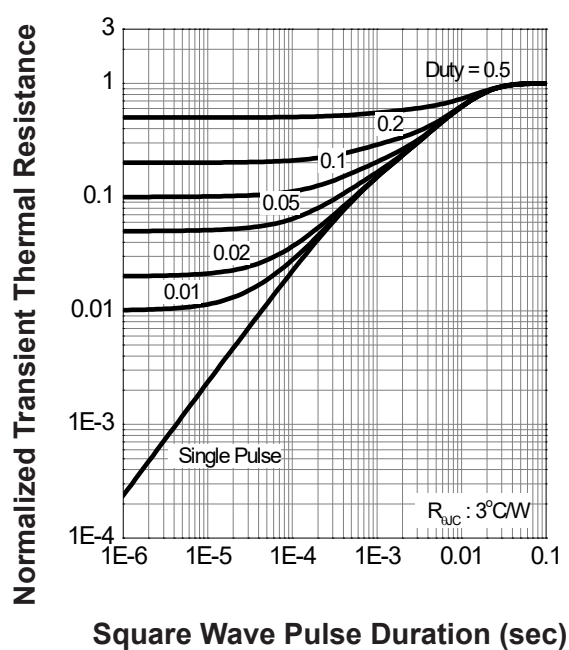
Drain Current



Safe Operation Area

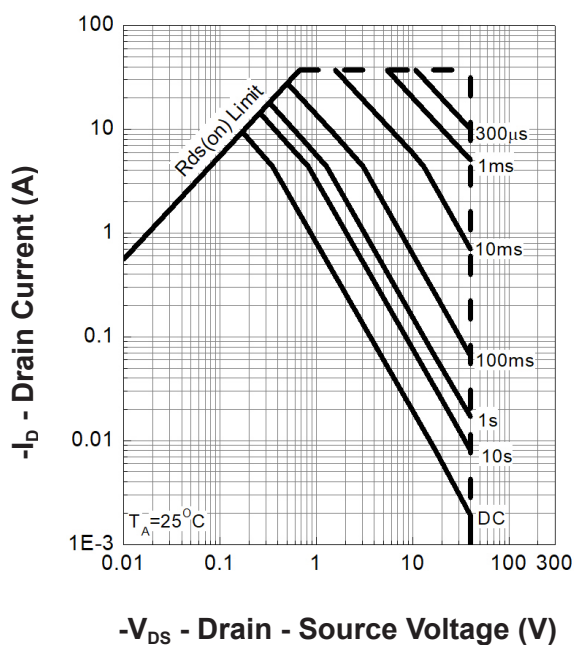


Thermal Transient Impedance

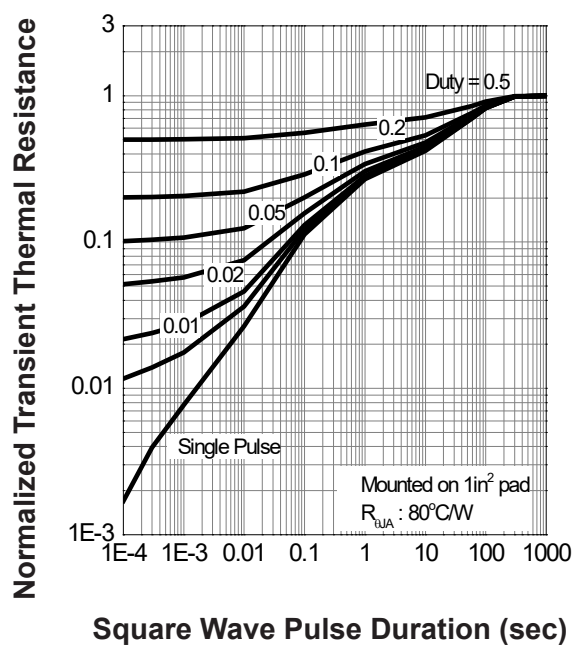


Typical Operating Characteristics(Cont.)

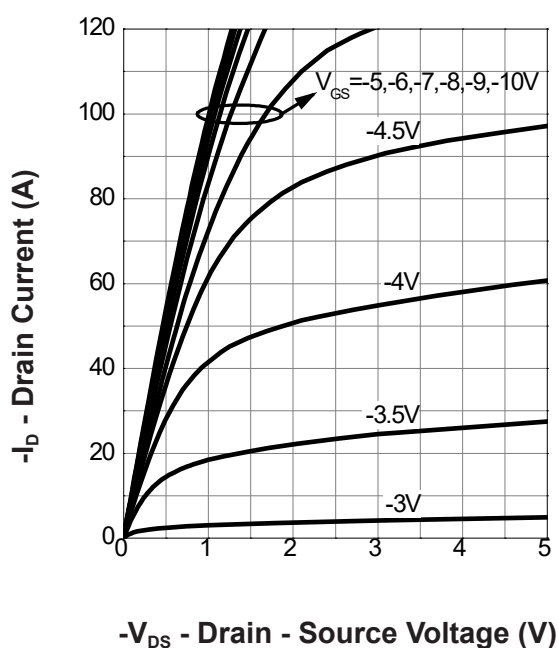
Safe Operation Area



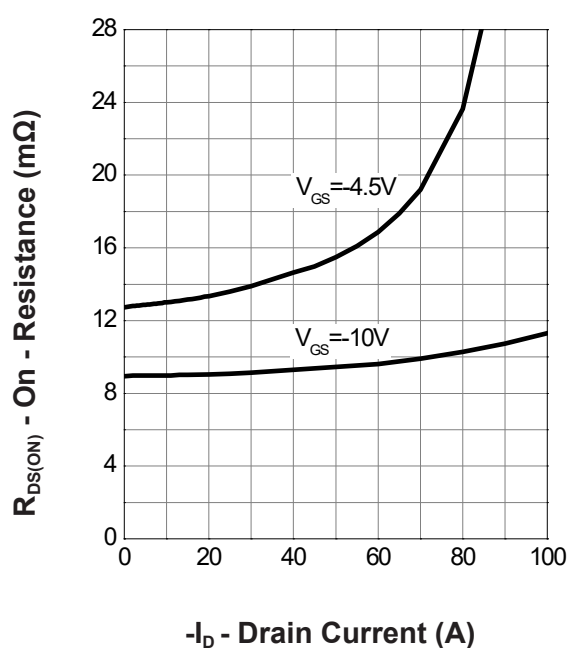
Thermal Transient Impedance



Output Characteristics

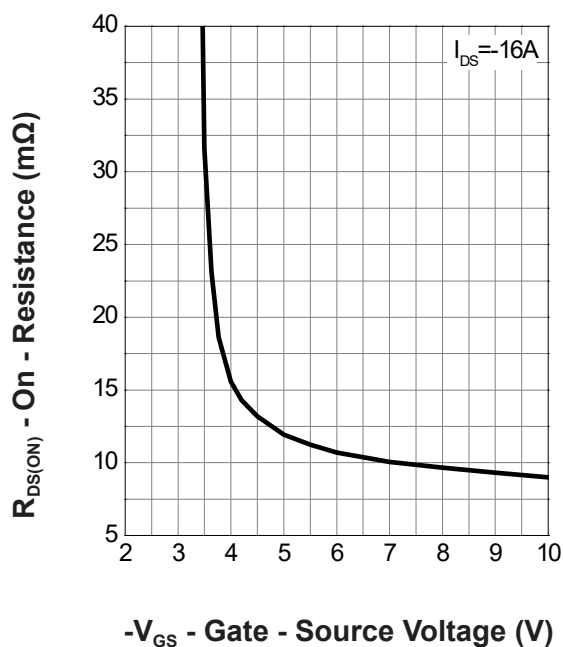


Drain-Source On Resistance

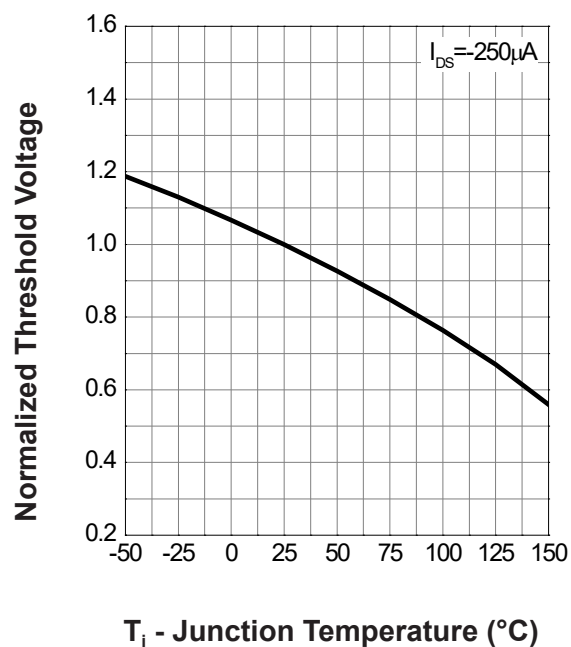


Typical Operating Characteristics(Cont.)

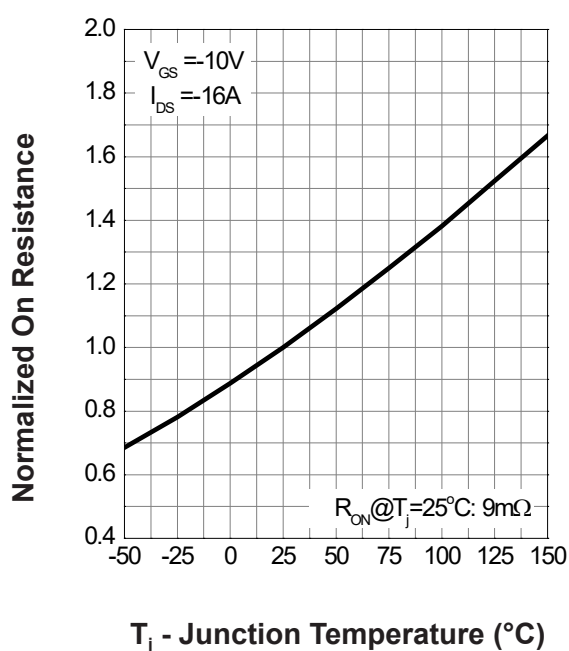
Gate-Source On Resistance



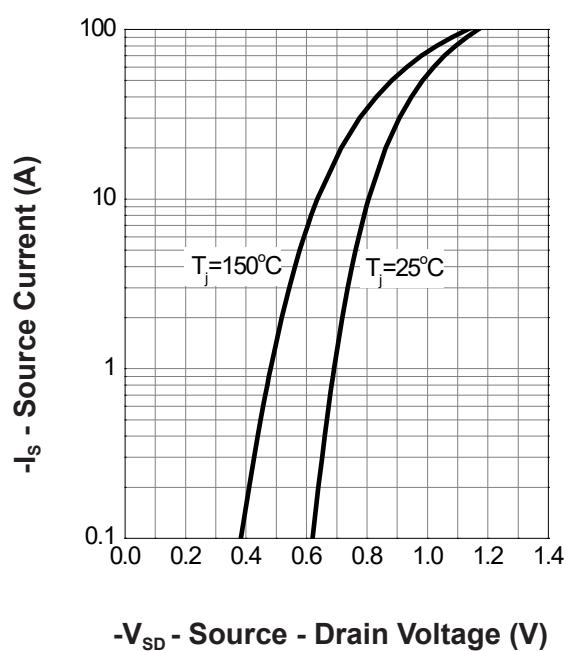
Gate Threshold Voltage



Drain-Source On Resistance

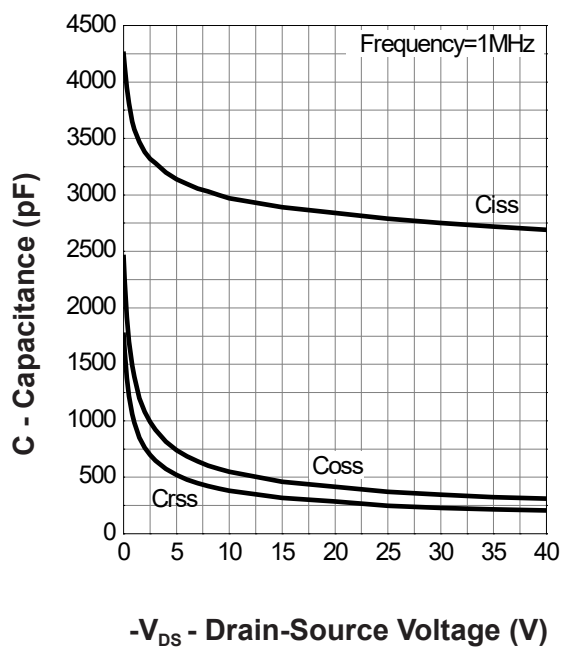


Source-Drain Diode Forward

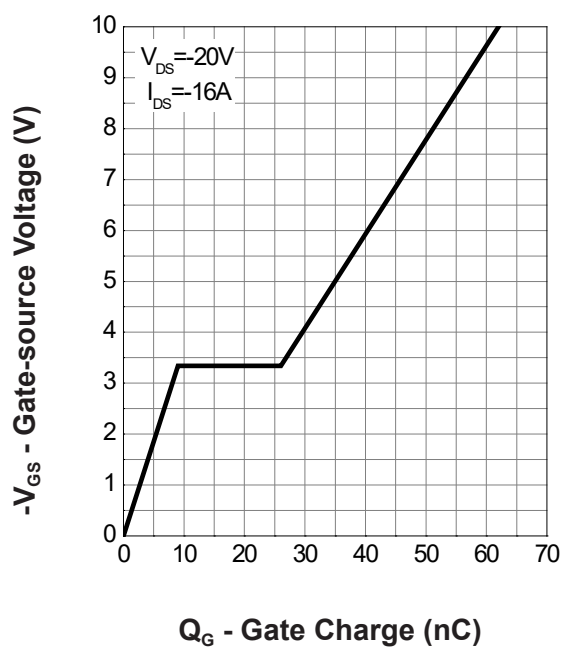


Typical Operating Characteristics(Cont.)

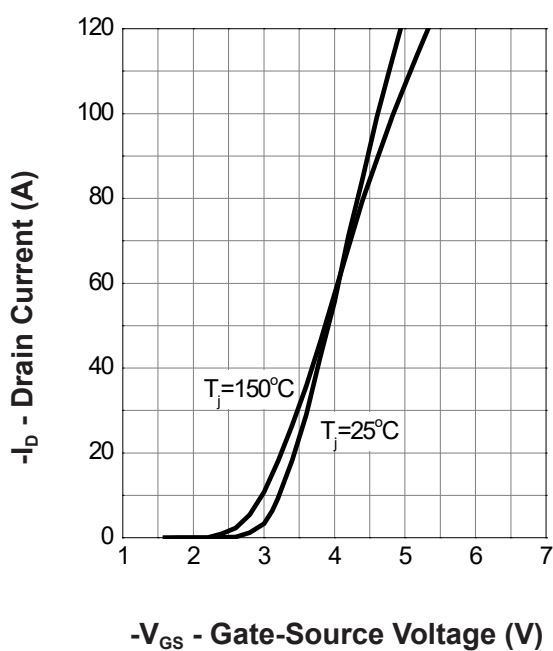
Capacitance



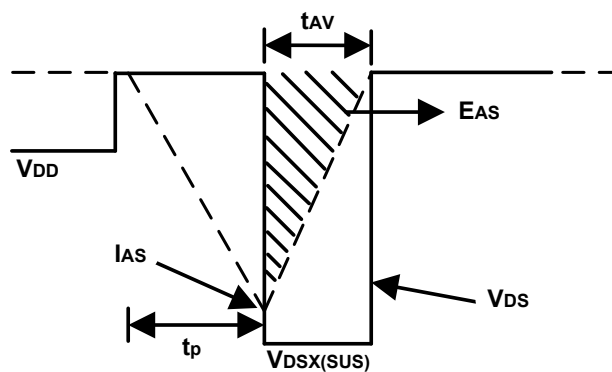
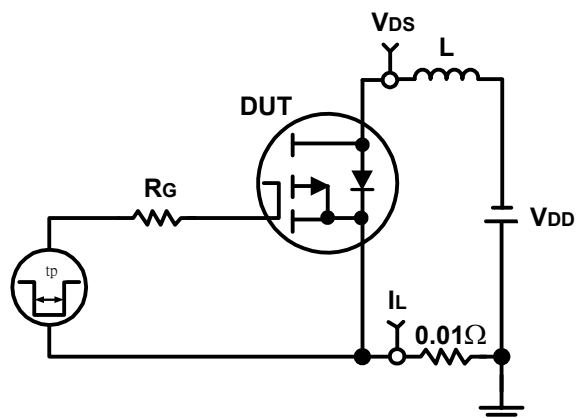
Gate Charge



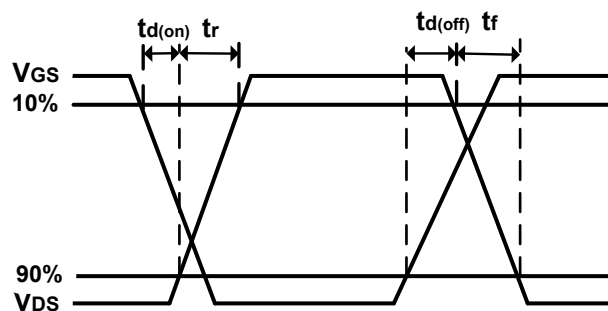
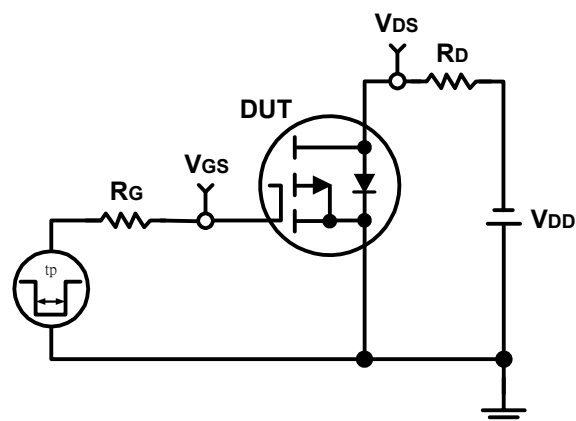
Transfer Characteristics



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



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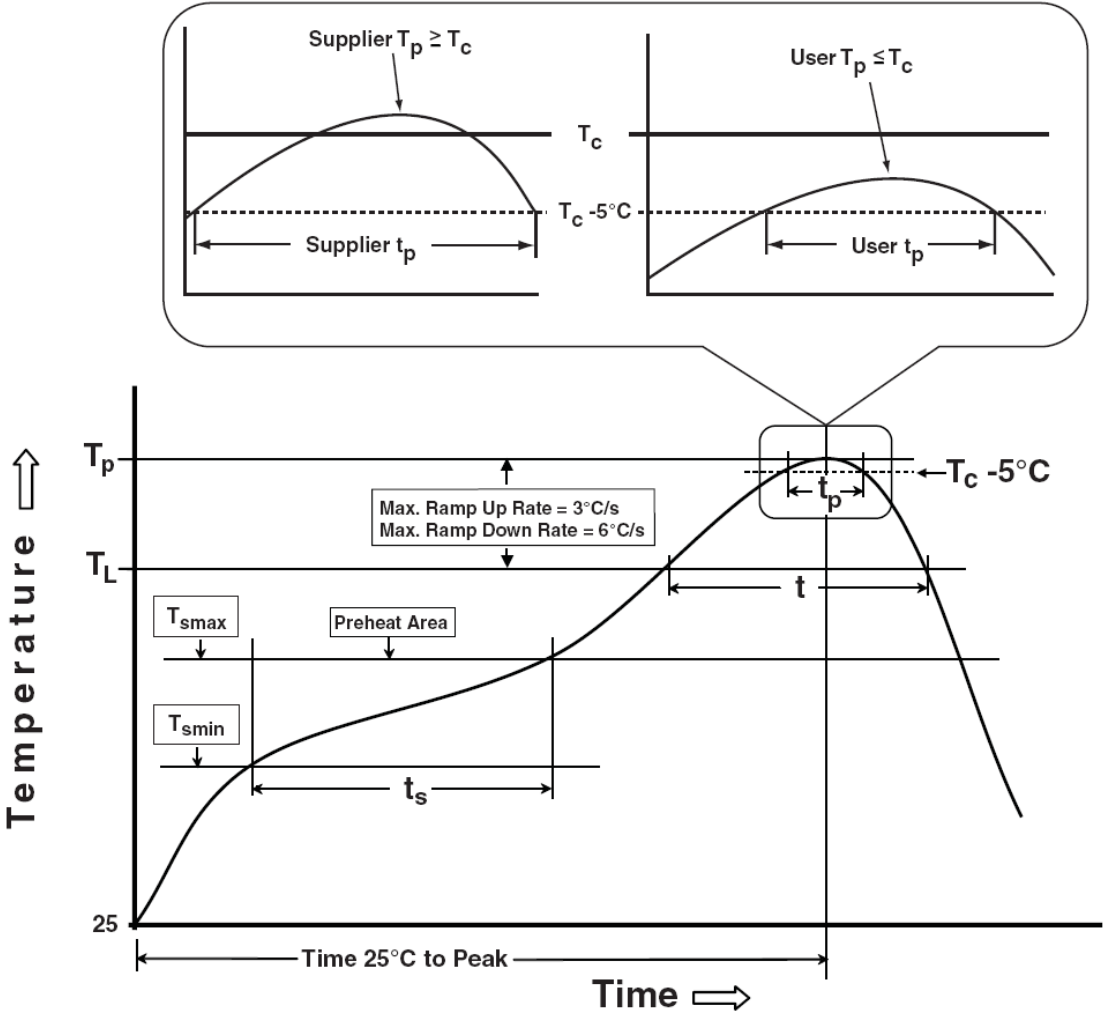
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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

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